

NPN Plastic-Encapsulate Transistors

Description

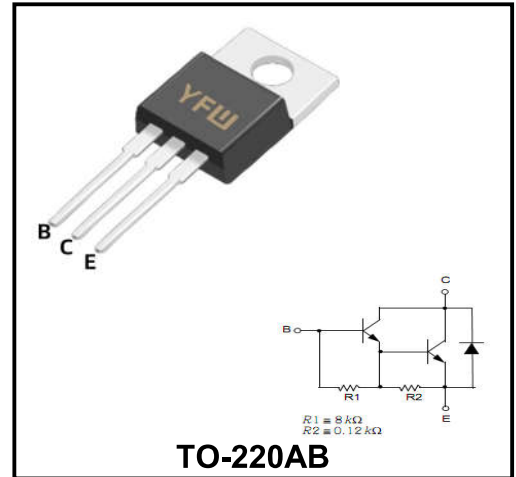
The devices are manufactured in planar technology with “base island” layout and monolithic Darlingtion configuration. The resulting transistors show exceptional high gain performance coupled with very low saturation voltage.

Applications

➤ General purpose linear and switching

Features

- Low collector-emitter saturation voltage
- Complementary to TIP125/126/127



Absolute Maximum Rating (Ta=25°C)

Parameter	Symbol	Value			Unit
		TIP120	TIP121	TIP122	
Collector-Base Voltage	BV_{CBO}	60	80	100	V
Collector-Emitter Voltage	BV_{CEO}	60	80	100	V
Emitter-Base Voltage	BV_{EBO}	5			V
Collector Current(DC)	I_C	5			A
Collector Dissipation	P_C	Ta =25 °C			W
		Tc =25 °C			
Junction Temperature	T_j	150			°C
Storage Temperature	T_{stg}	-65~150			°C

Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C = 30mA, I_B = 0$	60 80 100			V
Collector cut-off current	I_{CBO}	$V_{CB} = 60V, I_E = 0$ $V_{CB} = 80V, I_E = 0$ $V_{CB} = 100V, I_E = 0$			0.2	mA
Collector cut-off current	I_{CEO}	$V_{CE} = 30V, I_E = 0$ $V_{CE} = 40V, I_E = 0$ $V_{CE} = 50V, I_E = 0$			0.5	mA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			2	mA
* DC current gain	h_{FE}	$V_{CE} = 3V, I_C = 0.5A$ $V_{CE} = 3V, I_C = 3A$	1000 1000			
*Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 3A, I_B = 12mA$ $I_C = 5A, I_B = 20mA$			2.0 4.0	V
* Base-Emitter ON Voltage	$V_{BE(on)}$	$V_{CE} = 3V, I_C = 3A$			2.5	V
Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 0.1MHz$			200	pF

* Pulse Test : $PW \leq 300\mu s, Duty\ cycle \leq 2\%$

Typical Characteristics

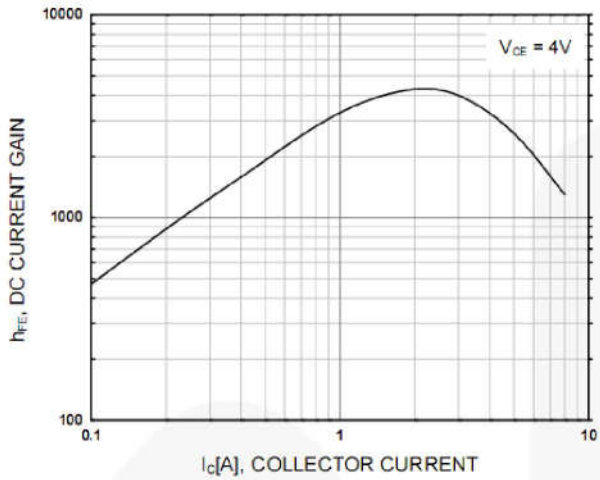


Figure 1. DC current Gain

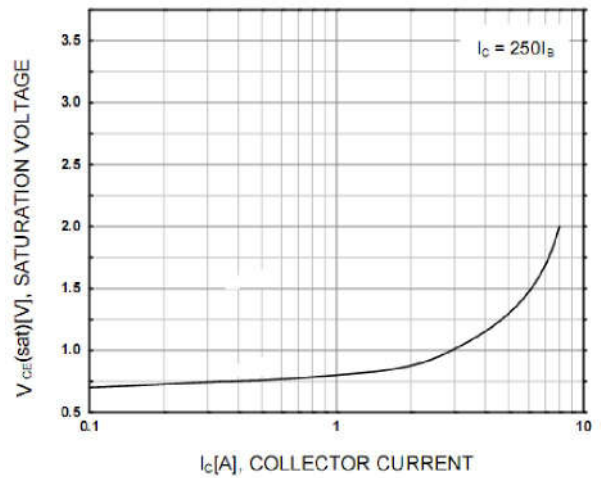


Figure 2. Collector-Emitter Saturation Voltage

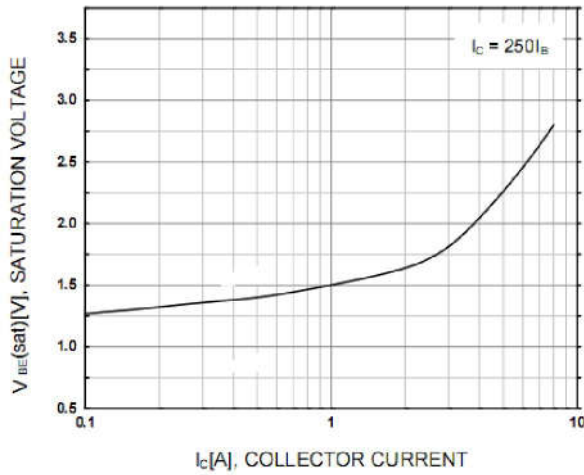


Figure 3. Base-Emitter Saturation Voltage

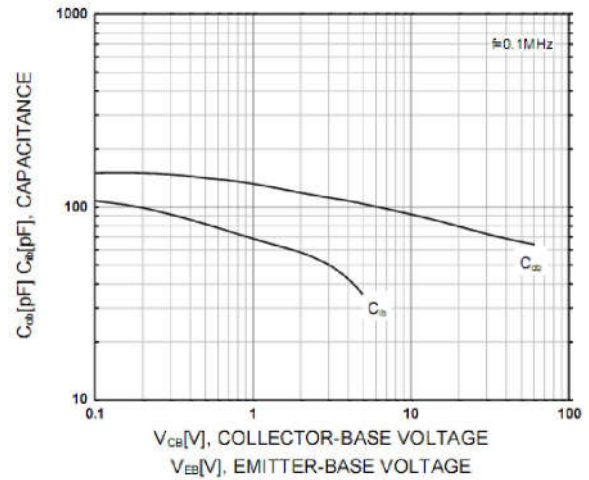


Figure 4. Output and Input Capacitance

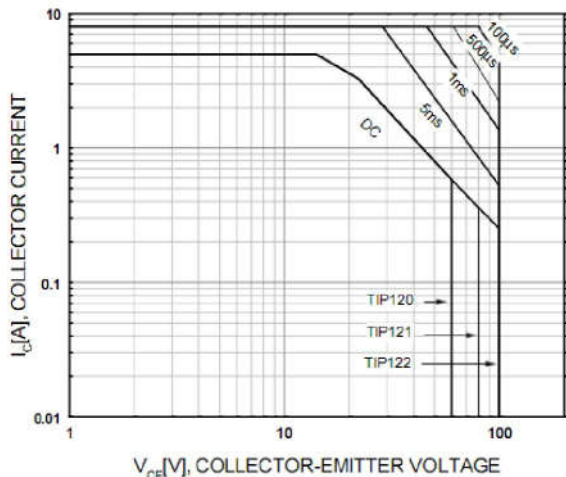


Figure 5. Safe Operating Area

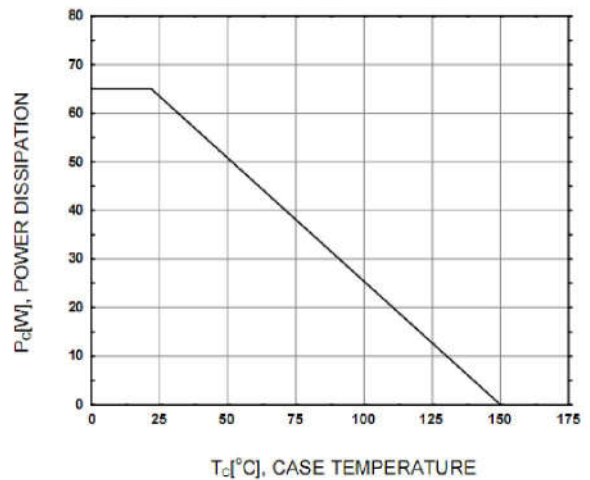
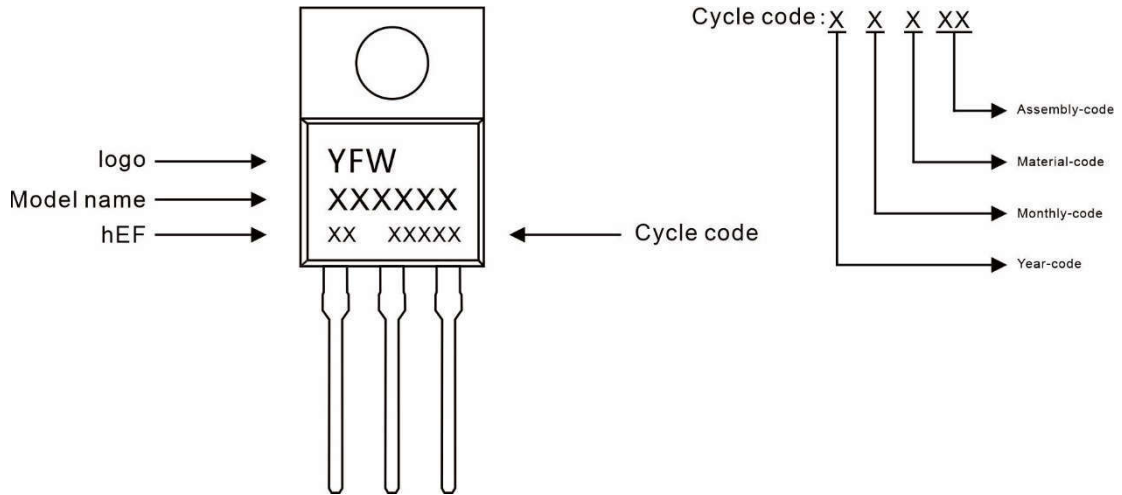


Figure 6. Power Derating

Marking Diagram



Ordering information

Model name	Package	Unit Weight	Base Quantity	Packing Quantity
TIPXXX	TO-220AB	0.07oz(1.96g)	50pcs/tube	1000PCS/Box 5000PCS/Carton

Package Dimensions
TO-220AB

Symbol	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.30	4.70	0.169	0.185
A1	2.52	2.82	0.099	0.111
b	0.71	0.91	0.028	0.036
b1	1.17	1.37	0.046	0.054
c	0.30	0.50	0.012	0.020
c1	1.17	1.37	0.046	0.054
D	9.90	10.20	0.390	0.402
E	8.50	8.90	0.335	0.350
E1	12.00	12.50	0.472	0.492
e	2.44	2.64	0.096	0.104
e1	4.88	5.28	0.192	0.208
F	2.60	2.80	0.102	0.110
L	13.20	13.80	0.520	0.543
L1	3.80	4.20	0.150	0.165
Φ	3.60	3.96	0.142	0.156

Disclaimer

The information presented in this document is for reference only. Guangdong Youfeng Microelectronics Co.,Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise. The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), YFW or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale. This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <https://www.yfwdiode.com>, or consult YFW sales office for further assistance.